

Silicon NPN Power Transistors

2SD552

DESCRIPTION

- With TO-3 package
- Complement to type 2SB552

APPLICATIONS

- Power amplifier applications
- Power switching applications
- DC-DC converters

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

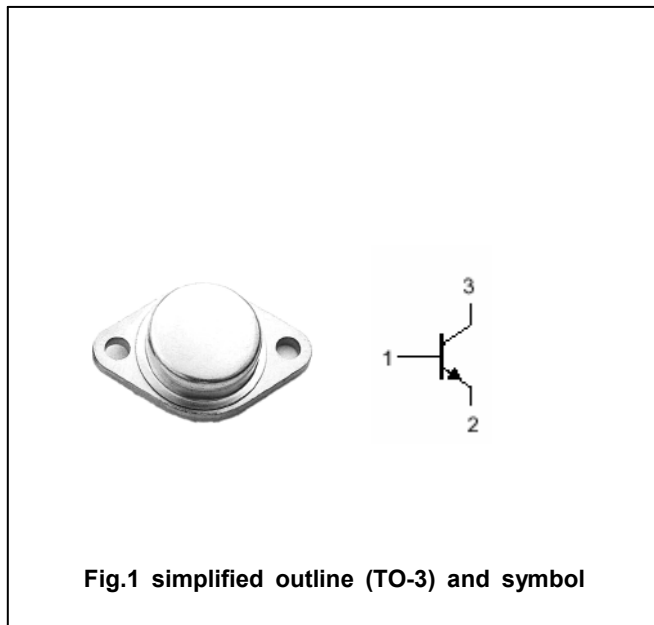


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	220	V
V_{CEO}	Collector-emitter voltage	Open base	180	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		15	A
I_B	Base current		4	A
P_C	Collector power dissipation	$T_C = 25 \square$	150	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-55~200	\square

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA ; I _B =0	180			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10A; I _B =1A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10A; I _B =1A			2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =220V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =5V	25		80	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V; f=1.0MHz		160		pF
f _T	Transition frequency	I _C =1A ; V _{CE} =10V	4			MHz

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)